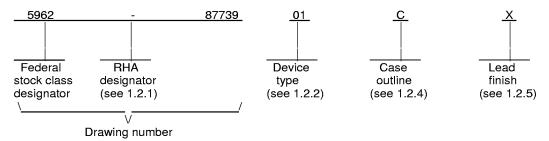
							F	REVIS	IONS										
LTR		DESCRIPTION								D,	ATE (\	/R-MO-I	DA)		APP	ROVE)		
Α		Make change to 1.3. Add vendor CAGE numbers 01295 and In accordance with N.O.R. 5962-R259-92.					nd 079	33.		92-0	09-24 M. A. FRY		. FRYE	Ē.,					
В	numb	Add class V devices and case outline X. Replace vendonumber 06665 with 24355. Make change to I _{IB} test and changes throughout. Redrawn										97-06-09 R. MONN			ONNIN	1			
С	Make	change	to dime	nsions	L, R, a	and R1	l as sp	pecifie	d in ca	se X .	- ro		97-1	2-17			R. M	ONNIN	I
D	Add r	radiation	hardnes	ss assu	rance	requir	ement	ts ro					98-0	06-17			R. M	ONNIN	1
E	Add o	device ty	pe 02 wi	ith radia	ation h	ardne	ss req	uireme	ents	ro.			98-1	0-29			R. M	ONNIN	1
F	Make	change	to table	IIB	ro								99-0	2-10			R. M	ONNIN	1
THE ORIGII	NAL FIRS	ST SHE	ET OF TI	HIS DF	RAWIN	G HAS	S BEE	N REF	PLACE	ED.	Ι	I		I	<u> </u>	I	T	1	
REV	NAL FIRS	ST SHE	ET OF TI	HIS DE	RAWIN	G HAS	S BEE	N REF	PLACE	D.									
	NAL FIRS	ST SHEI	ET OF TI	HIS DE	RAWIN	G HAS	S BEE	N REF	PLACE	D.									
REV SHEET	NAL FIRS	ST SHE	ET OF TI	HIS DE	AWIN	G HAS	S BEE	N REF	PLACE	D.									
REV SHEET REV SHEET REV STAT	TUS	ST SHEI	ET OF TI		AWIN	G HAS	S BEE	N REF	PLACE	F.	F	F	F	F	F	F	F	F	F
REV SHEET REV SHEET	TUS	ST SHEI	RE		AWIN						F 6	F 7	F 8	F 9	F 10	F 11	F 12	F 13	F 14
REV SHEET REV SHEET REV STAT	TUS	ST SHEI	RE SH	EV	ED BY	F 1	F	F	F	F 5		7 NSE S	8 UPPL	9 Y CEN	10	11 COLU	12	13	
REV SHEET REV SHEET REV STAT OF SHEET PMIC N/A STA MICR	TUS	RD	RE SH PR JC	EV EET	ED BY A. KE	F 1	F 2	F	F	F 5	6	7 NSE S	8 UPPL	9 Y CEN	10	11 COLU	12	13	
REV SHEET REV SHEET REV STAT OF SHEET PMIC N/A STA MICR DR THIS I	US	RD CUIT IG	RE SH PR JC	EV IEET EPARE DSEPH	ED BY A. KE	F 1	F 2	F	F 4	F 5	6 DEFEI	7 NSE S COL	8 UPPL UMBI	9 Y CEN JS, OH	10 NTER HIO 4:	11 COLU 3216	12 MBUS	13	14
REV SHEET REV SHEET REV STAT OF SHEET PMIC N/A STA MICRO DR THIS I	ANDAF OCIRO RAWIN PAILABLE USE BY ARTMEN ENCIES O	RD CUIT IG G IS E ALL ITS OF THE	RE SH PR JC CH D/ API M	EPARE DSEPH ECKEL AVID H	ED BY A. KE D BY I. JOHI	F 1 RBY NSON	F 2	F 3	F 4	F 5	6 DEFEI	7 NSE S COL	8 UPPL UMBI NEAR	9 Y CEN JS, OH	10 NTER HIO 4:	11 COLU 3216 OLTA	12 MBUS	13	14 ΓHIC
REV SHEET REV SHEET REV STAT OF SHEET PMIC N/A STA MICRI DR THIS I AV FOR DEP AND AGE DEPARTME	ANDAF OCIRO RAWIN PAILABLE USE BY ARTMEN ENCIES O	RD CUIT IG G IS E ALL ITS OF THE	RE SH PR JC CH D/	EPARE DSEPH ECKEL AVID H	ED BY A. KE D BY I. JOHI	F 1 RBY NSON RYE ROVA	F 2	F 3	F 4 MIC CON SILI	F 5	6 PEFEI	7 NSE S COL	8 UPPL UMBI	9 Y CEN JS, OH	10 NTER HIO 4:	11 COLU 3216 OLTA	12 MBUS	13	14 ΓHIC

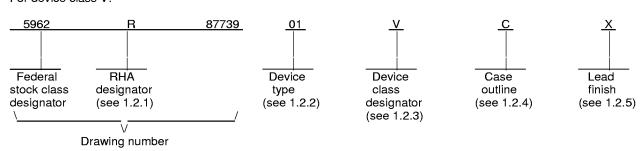
1. SCOPE

- 1.1 <u>Scope</u>. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.
 - 1.2 PIN. The PIN is as shown in the following examples.

For device classes M and Q:



For device class V:



- 1.2.1 <u>RHA designator</u>. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.
 - 1.2.2 <u>Device type(s)</u>. The device type(s) identify the circuit function as follows:

Device type	Generic number	<u>Circuit function</u>		
01	LM139A	Quad voltage comparator		
02	LM139	Quad voltage comparator		

1.2.3 <u>Device class designator</u>. The device class designator is a single letter identifying the product assurance level as listed below. Since the device class designator has been added after the original issuance of this drawing, device classes M and Q designators will not be included in the PIN and will not be marked on the device.

Device class	Device requirements documentation
М	Vendor self-certification to the requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A
Q or V	Certification and qualification to MIL-PRF-38535

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1.2.4 <u>Case outline(s)</u>. The case outline(s) are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
С	GDIP1-T14 or CDIP2-T14	14	Dual-in-line
D	GDFP1-F14 or CDFP2-F14	14	Flat pack
Χ	See figure 1	14	Flat pack
2	CQCC1-N20	20	Square leadless chip carrier

1.2.5 <u>Lead finish</u>. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

1.3 Absolute maximum ratings. 1/

Supply voltage range	r ±18 V dc
Input voltage range0.3 V dc	
Input current (V _{IN} < -0.3 V)	
Maximum power dissipation (P _D) 900 mW	<u>2</u> /
Sink current	
Lead temperature (soldering 10 seconds) 300°C	
Storage temperature65°C to +	⊦150°C
Junction temperature (T _J)	
Thermal resistance, junction-to- case (Θ_{IC}) :	
Cases C, D, and 2 See MIL-S	STD-1835
Case X	

1.4 Recommended operating conditions.

Supply voltage 5 V dc to 30 V dc Ambient operating temperature range (T_A) -55° C to +125° C

1.5 Radiation features.

2. APPLICABLE DOCUMENTS

2.1 <u>Government specification, standards, and handbooks</u>. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement thereto, cited in the solicitation.

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

- Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.
- 2/ Derate above 100°C ambient, 10mW/°C.

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STANDARDS

DEPARTMENT OF DEFENSE

MIL-STD-883 - Test Methods and Procedures for Microelectronics.

MIL-STD-973 - Configuration Management. MIL-STD-1835 - Microcircuit Case Outlines.

HANDBOOKS

DEPARTMENT OF DEFENSE

MIL-HDBK-103 - List of Standard Microcircuit Drawings (SMD's).

MIL-HDBK-780 - Standard Microcircuit Drawings.

(Unless otherwise indicated, copies of the specification, standards, and handbooks are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.
 - 3.2.1 Case outline(s). The case outline(s) shall be in accordance with 1.2.4 herein and on figure 1.
 - 3.2.2 Terminal connections. The terminal connections shall be as specified on figure 2.
 - 3.2.3 Logic diagram. The logic diagram shall be as specified on figure 3.
 - 3.2.4 Radiation exposure circuit. The radiation exposure circuit shall be as specified on figure 4.
- 3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table I.
- 3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked as listed in MIL-HDBK-103. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.
- 3.5.1 <u>Certification/compliance mark</u>. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.

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TABLE I. <u>Electrical performance characteristics</u>.

Test	Symbol		ditions	Group A	Device	Liı	nits	Unit
		-55°C≤ 1 _/ unless otherw	ղ ≤ +125°C vise specified	subgroups	type	Min	Max	
Input offset voltage	V _{IO}	$R_s = 0 \Omega, V_o$	= 1.4 V,	1	01		±2.0	mV
		V+ = 5 V dc to	o 30 V dc	2,3]		±4.0	
			M,D,L,R <u>1</u> /	1			±3.0	
		$R_s = 0 \Omega, V_o$	= 1.4 V,	1	02		±5.0	
		V+ = 5 V dc to	o 30 v ac	2,3			±9.0	
		M,D,L,R <u>1</u> / 1			±6.0			
Input offset current	I _{IO}	I _{IN+} - I _{IN-} with	output in	1	All		±25	nA
		the linear ran	linear range				±100	
			M,D,L,R <u>1</u> /	1			±25	
Input bias current	I _{IB}	I _{IN+} or I _{IN-} w	I _{IN+} or I _{IN-} with output in the linear range		All		+100	nA
		the linear ran					+300	
			M,D,L,R <u>1</u> /	1			±100	
Input common-mode <u>2</u> /voltage range	V _{ICR}	V+ = 5 V to 3	0 V	1,2,3	All	0	V+ -2.0	V
Voltage gain 2/	A _V	$R_L \ge 15 \text{ k}\Omega, V+ = 15 \text{ V}$		4	All	50		V/mV
				5,6		25		
Output sink current 2/	I _{SINK}	$V_{IN-} = 1 \text{ V, } V_{I}$ $V_{O} \ge 1.5 \text{ V, } T$	_{IN+} = 0 V, _A = 25°C	1	All	6		mA
Saturation voltage	V _{SAT}	V _{IN-} = 1 V, V	_{IN+} = 0 V, <u>2</u> /	1	All		400	mV
		ISINK ≤ 4 MA	I _{SINK} ≤ 4 mA				700	
		$V_{IN-} \le 1 \text{ V, V}_{IO}$ $I_{O} = 4 \text{ mA}$	_{IN+} = 0 V,	1			400	
			M,D,L,R <u>1</u> /	1			400	1
Output leakage current	l _{OL}	V _{IN+} ≥ 1 V do V _{IN-} = 0 V	c, V _O = 30 V,	1	All		0.5	μА
		ν _{IN-} = 0 ν		2,3			1	
			M,D,L,R <u>1</u> /	1			0.5	

See footnotes at end of table I.

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TABLE I. Electrical performance characteristics - Continued.

Test	Symbol Conditions		Group A	Device	Limits		Unit	
		-55°C ≤ T _A ≤ +125°C unless otherwise specified		subgroups	type	Min	Max	
Supply current	I _{CC}	R _L = ∞, V+ = 5	R _L = ∞, V+ = 5 V to 30 V		All		3	mA
			M,D,L,R <u>1</u> /	1	All		2	
Input voltage common <u>2/</u> mode rejection ratio	CMRR	$R_L \ge 15 \text{ k}\Omega, V + = 30 \text{ V}, V_{CM} = 0 \text{ V to } 28 \text{ V}$		1,2,3	All	70		dB
Power supply rejection ratio	PSRR	V+ = 5 V to 3	0 V <u>2</u> / <u>3</u> /	1,2,3	All	70		dB
Response time 2/	t _{RLH}	$V_{RL} = 5 \text{ V}, R_L = 5.1 \text{ k}\Omega,$ 100 mV input step, $T_A = +25^{\circ}\text{C}$		9	All		5	μѕ
	t _{RHL}	5 mV overdriv T _A = +25°C	/e,	9			2.5	

- Devices supplied to this drawing have been characterized through all levels M, D, L, and R of irradiation. However, this device is only tested at the "R" level. Pre and Post irradiation values are identical unless otherwise specified in table I. When performing post irradiation electrical measurements for any RHA level, T_A = +25°C.
- 2/ This parameter is not tested to post irradiation.
- 3/ Guaranteed, if not tested, to the limits specified in table I.
- 3.6 <u>Certificate of compliance</u>. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 <u>Notification of change for device class M.</u> For device class M, notification to DSCC-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-STD-973.
- 3.9 <u>Verification and review for device class M.</u> For device class M, DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
- 3.10 <u>Microcircuit group assignment for device class M.</u> Device class M devices covered by this drawing shall be in microcircuit group number 050 (see MIL-PRF-38535, appendix A).

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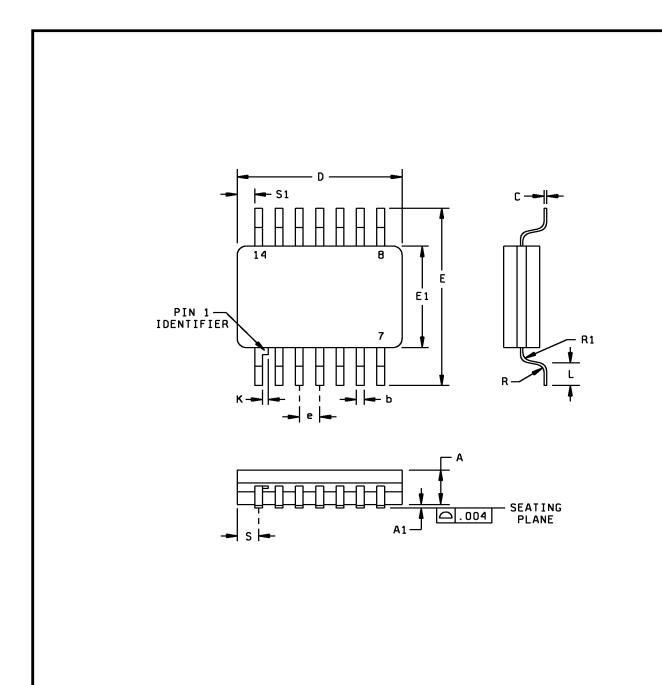


FIGURE 1. Case outline.

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Letter	Inches		Inches Millimeters		Notes
	Min	Max	Min	Max	
Α	.050	.080	1.27	2.03	
A1	.004	.012	0.10	0.30	
b	.015	.019	0.38	0.48	2
С	.004	.008	0.10	0.20	2
D		.385		9.78	
E		.420		10.67	
E1	.245	.270	6.22	6.86	
е		.050 BSC		1.27 BSC	
К	.007	.012	0.18	0.30	
L	.037	.043	0.94	1.09	
R	.013	.017	0.33	0.43	
R1	.013	.017	0.33	0.43	
S		.045		1.14	
S1	.005		0.13		

NOTES:

- 1. The U.S. government preferred system of measurement is the metric SI system. However, since this item was originally designed using inch pound units of measurement, in the event of conflict between the metric and inch-pound units, the inch-pound units shall take precedence.
- 2. Maximum limit may be increased by .003 inches after lead finish is applied.

FIGURE 1. Case outline - Continued.

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Device type	01		
Case outlines	C , D, and X	2	
Terminal number	Termina	l symbol	
1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16 17 18 19 20	OUT 2 OUT 1 V+ IN 1- IN 1+ IN 2- IN 2+ IN 3- IN 3+ IN 4- IN 4+ GND OUT 4 OUT 3	NC OUT 2 OUT 1 V+ NC IN 1- NC IN 1+ IN 2- IN 2+ NC IN 3- IN 3- IN 3+ IN 4- NC IN 4- NC GND OUT 4 OUT 3	

FIGURE 2. Terminal connections.

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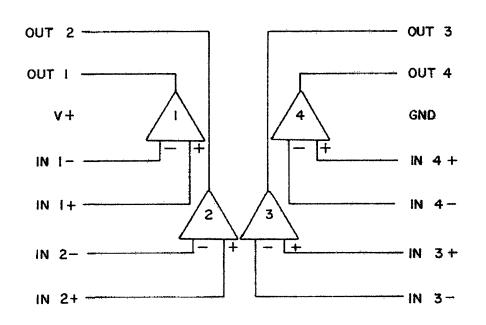


FIGURE 3. Logic diagram.

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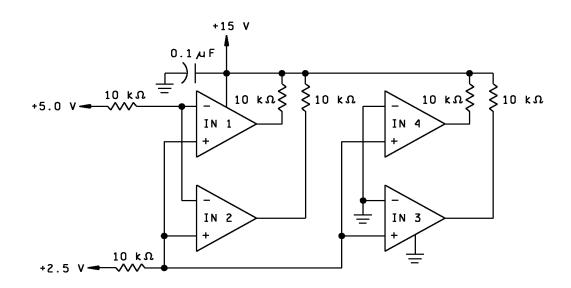


FIGURE 4. Radiation Exposure Circuit.

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4. QUALITY ASSURANCE PROVISIONS

- 4.1 <u>Sampling and inspection</u>. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.
- 4.2 <u>Screening</u>. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.
 - 4.2.1 Additional criteria for device class M.
 - a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
 - (2) $T_A = +125^{\circ}C$, minimum.
 - b. Interim and final electrical test parameters shall be as specified in table IIA herein.
 - 4.2.2 Additional criteria for device classes Q and V.
 - a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
 - b. Interim and final electrical test parameters shall be as specified in table IIA herein.
 - Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.
- 4.3 <u>Qualification inspection for device classes Q and V</u>. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).
- 4.4 <u>Conformance inspection</u>. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified herein except where option 2 of MIL-PRF-38535 permits alternate in-line control testing. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).
 - 4.4.1 Group A inspection.
 - a. Tests shall be as specified in table IIA herein.
 - Subgroups 7, 8, 10, and 11 in table I, method 5005 of MIL-STD-883 shall be omitted.

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TABLE IIA. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	Subgroups (in accordance with MIL-PRF-38535, table III)	
	Device class M	Device class Q	Device class V
Interim electrical parameters (see 4.2)	1	1	1
Final electrical parameters (see 4.2)	1,2,3,4,5,6,9 <u>1</u> /	1,2,3,4,5,6,9 <u>1</u> /	1,2,3,4,5, <u>1</u> / <u>2</u> / 6,9
Group A test requirements (see 4.4)	1,2,3,4,5,6,9	1,2,3,4,5,6,9	1,2,3,4,5,6,9
Group C end-point electrical parameters (see 4.4)	1,2,3	1,2,3	1,2,3 <u>2</u> /
Group D end-point electrical parameters (see 4.4)	1,2,3	1,2,3	1,2,3
Group E end-point electrical parameters (see 4.4)			1

^{1/} PDA applies to subgroup 1.

TABLE IIB. 240 hours and group C operating life deltas.

Test	Symbol	Device				Units
		type	Min	Max	Delta	
Input offset voltage	v _{IO}	01	-2	2	±1.5	mV
		02	-5	5	±2.0	
Input bias current	I _{IB}	All	-100	100	±15	nA

- 4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table IIA herein.
- 4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:
 - a. Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
 - b. $T_A = +125^{\circ}C$, minimum.
 - c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

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^{2/} Delta limits as specified in table IIB shall be required where specified, and the delta limits shall be computed with reference to the previous interim electrical parameters.

- 4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
 - 4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table II herein.
- 4.4.4 <u>Group E inspection</u>. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein). RHA levels for device classes M, Q, and V shall be as specified in MIL-PRF-38535. End-point electrical parameters shall be as specified in table IIA herein.
- 4.4.4.1 <u>Total dose irradiation testing</u>. Total dose irradiation testing shall be performed in accordance with MIL-STD-883 method 1019 and as specified herein.
- 4.4.4.1.1 <u>Accelerated aging test</u>. Accelerated aging tests shall be performed on all devices requiring a RHA level greater than 5k rads(Si). The post-anneal end-point electrical parameter limits shall be as specified in table I herein and shall be the pre-irradiation end-point electrical parameter limit at 25°C ±5°C. Testing shall be performed at initial qualification and after any design or process changes which may affect the RHA response of the device.
- 4.4.4.2 <u>Dose rate burnout</u>. When required by the customer test shall be performed on devices, SEC, or approved test structures at technology qualifications and after any design or process changes which may effect the RHA capability of the process. Dose rate burnout shall be performed in accordance with test method 1023 of MIL-STD-883 and as specified herein.

5. PACKAGING

5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

6. NOTES

- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
- 6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-973 using DD Form 1692, Engineering Change Proposal.
- 6.3 <u>Record of users</u>. Military and industrial users should inform Defense Supply Center Columbus when a system application requires configuration control and which SMD's are applicable to that system. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0525.
- 6.4 <u>Comments</u>. Comments on this drawing should be directed to DSCC-VA, Columbus, Ohio 43216-5000, or telephone (614) 692-0674.
- 6.5 <u>Abbreviations, symbols, and definitions</u>. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.
 - 6.6 Sources of supply.
- 6.6.1 <u>Sources of supply for device classes Q and V</u>. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agreed to this drawing.
- 6.6.2 Approved sources of supply for device class M. Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-87739
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216		REVISION LEVEL F	SHEET 14

STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 99-02-10

Approved sources of supply for SMD 5962-87739 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535.

Standard microcircuit drawing PIN <u>1</u> /	Vendor CAGE number	Vendor similar PIN <u>2</u> /
5962-8773901CA	01295	LM139AJB
	07933	LM139AD/883
	27014	LM139AJ/883
	24355	PM-139AY/883
5962-8773901DA	01295	LM139AWB
	27014	LM139AW/883
5962-8773901XA	27014	LM139AWG/883
5962-87739012A	01295	LM139AFKB
	24355	PM-139ARC/883
	27014	LM139AE/883
5962-8773901VCA	24355	PM139AY/QMLV
5962-8773901VDA	24355	PM139AM/QMLV
5962-8773901V2A	24355	PM139ARC/QMLV
5962R8773901VCA	24355	PM139AY/QMLR
5962R8773901VDA	24355	PM139AM/QMLR
5962R8773901V2A	24355	PM139ARC/QMLR

Standard microcircuit drawing PIN <u>1</u> /	Vendor CAGE number	Vendor similar PIN <u>2</u> /
5962R8773902VCA	24355	PM139Y/QMLR
5962R8773902VDA	24355	PM139M/QMLR
5962R8773902V2A	24355	PM139RC/QMLR

- 1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed, contact the vendor to determine its availability.
- contact the vendor to determine its availability.

 2/ Caution. Do not use this number for item acquisition.

 Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE number	Vendor name and address
01295	Texas Instruments, Incorporated 6412 Highway 75 South Sherman, TX 75090-0084
07933	Raytheon Company Semiconductor Division 350 Ellis Street P.O. Box 7016 Mountain View, CA 94039-7016
24355	Analog Devices, Incorporated RT 1 Industrial Park PO Box 9106 Norwood, MA 02062 Point of contact: 1500 Space Park Drive P.O. Box 58020 Santa Clara, CA 95050-8020
27014	National Semiconductor Corporation 2900 Semiconductor Drive P.O. Box 58090 Santa Clara, CA 95052-8090

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.